

# **isc Silicon NPN Power Transistors**

## TIP29B

#### **DESCRIPTION**

- · Collector-Emitter Sustaining Voltage-
  - $: V_{CEO(SUS)} = 80V(Min)$
- · Collector-Emitter Saturation Voltage-
  - :  $V_{CE(sat)} = 0.7V(Max.)@I_C = 1.0A$
- Complement to Type TIP30B
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

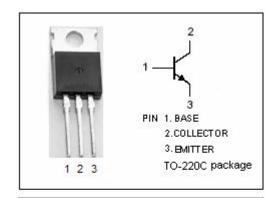
• Designed for use in general purpose amplifier and switching applications.

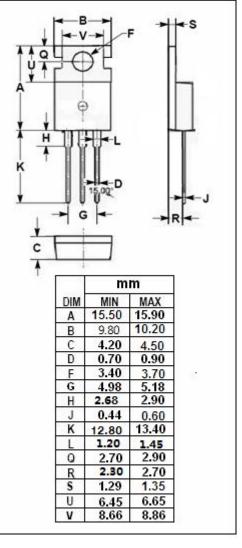
## ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	80	V
V <sub>CEO</sub>	Collector-Emitter Voltage	80	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
Ic	Collector Current-Continuous	1	А
Ісм	Collector Current-Pulse	3	А
lΒ	Base Current	0.4	А
Pc			W
T <sub>j</sub>	Junction Temperature 150		$^{\circ}$
T <sub>stg</sub>	Storage Ttemperature Range	-65~150	$^{\circ}$

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	4.17	°C/W
R <sub>th j-a</sub>	Thermal Resistance,Junction to Ambient	62.5	°C/W







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 30mA; I <sub>B</sub> = 0	80		V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 0.125A		0.7	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 1A; V <sub>CE</sub> = 4V		1.3	V
Ices	Collector Cutoff Current	V <sub>CE</sub> = 80V; V <sub>EB</sub> = 0		0.2	mA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 80V; I <sub>B</sub> = 0		0.3	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0		1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.2A; V <sub>CE</sub> = 4V	40		
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 4V	15	75	
fτ	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.2A; V <sub>CE</sub> = 10V; f= 1MHz	3		MHz

### **NOTICE:**

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